



30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	20.5mΩ @ V _{GS} = 10V	8.3A
30V	30mΩ @ V _{GS} = 4.5V	7.4A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- **Power Management Functions**

Features and Benefits

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

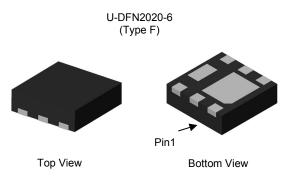
https://www.diodes.com/products/automotive/automotiveproducts/.

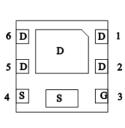
This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

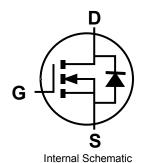
https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0065 grams (Approximate)







Pinout **Bottom View**

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3025LFDF-7	U-DFN2020-6 (Type F)	3000/Tape & Reel
DMN3025LFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information

Site1



S6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2017	20	18	2019	2020	20	21	2022	2023	20	24	2025
Code	Е	F	=	G	Н		I	J	K		L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2



S6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = week 27; z represents week 52 and 53) X = Internal code (ex: U = Monday)

Date Code Key

Ī	Year	2019	2020	2021	2022	2023	2024	2025	2026
	Code	9	0	1	2	3	4	5	6

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Y	Z

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) // = 10\/	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	8.3 6.6	А
Continuous Drain Current (Note 6) V _{GS} = 10V	t < 10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	9.9 7.9	А
Maximum Continuous Body Diode Forward Curre	nt (Note 6)		I _S	3	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	I _{DM}	40	Α		
Avalanche Current (L = 0.1mH) (Note 7)	I _{AS}	15	Α		
Avalanche Energy (L = 0.1mH) (Note 7)	Eas	11	mJ		

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Dawer Dissination (Note 5)	T _A = +25°C		0.66	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	P_{D}	0.42	VV	
Thormal Desigtance Junction to Ambient (Note 5)	Steady State	П	173	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t < 10s	$R_{\theta JA}$	133		
Total Power Dissipation (Note 6)	T _A = +25°C	Б	2.1	W	
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	P_{D}	1.3		
Thormal Posistance Junation to Ambient (Note 6)	Steady State	П	62	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{\theta JA}$	43		
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	9.4	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV_{DSS}	30		_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_		1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	1.0		2.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_		20.5	mΩ	$V_{GS} = 10V, I_D = 7A$	
Static Dialii-Source Off-Resistance	R _{DS(ON)}	_	_	30	11122	$V_{GS} = 4.5V, I_D = 7A$	
Diode Forward Voltage	V_{SD}	_	0.70	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C_{iss}	_	641	_		15)()(
Output Capacitance	Coss	_	66	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	50	_		1 - 1.0WH 12	
Gate Resistance	R_g	_	2.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	6	_			
Total Gate Charge (V _{GS} = 10V)	Q_g	_	13.2	_	nC	\/ - 45\/ - 400	
Gate-Source Charge	Q_{gs}	_	1.7	_	IIC	$V_{DS} = 15V, I_{D} = 10A$	
Gate-Drain Charge	Q _{gd}	_	2.2	_			
Turn-On Delay Time	t _{D(ON)}	_	3.3	_			
Turn-On Rise Time	t _R		4.4	_		V _{DD} = 15V, V _{GS} = 10V,	
Turn-Off Delay Time	t _{D(OFF)}	_	22.3	_	ns	$R_G = 6\Omega$, $I_D = 1A$	
Turn-Off Fall Time	t _F	_	5.3	_			
Reverse Recovery Time	t _{RR}	_	11.4	_	ns	I _F = 11A, di/dt = 100A/μs	
Reverse Recovery Charge	Q _{RR}	_	8.2	_	nC	I _F = 11A, di/dt = 100A/µs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{7.} I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.

^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.



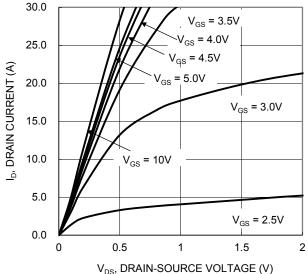


Figure 1. Typical Output Characteristic

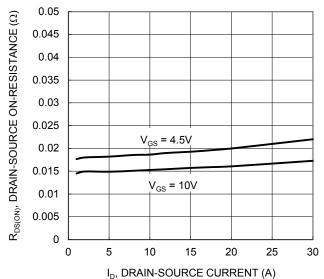


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

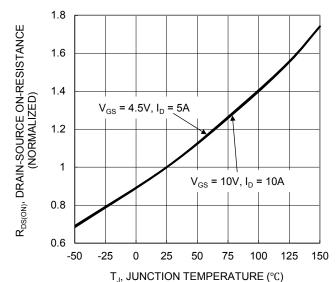


Figure 5. On-Resistance Variation with Temperature

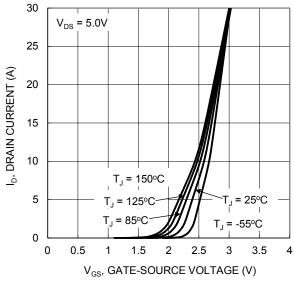


Figure 2. Typical Transfer Characteristic

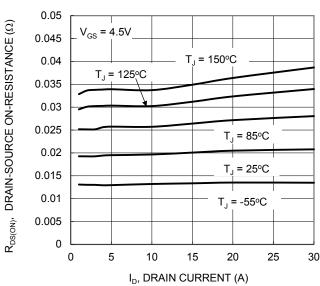


Figure 4. Typical On-Resistance vs Drain Current and Temperature

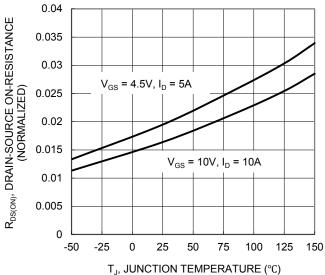


Figure 6.On-Resistance Variation with Temperature



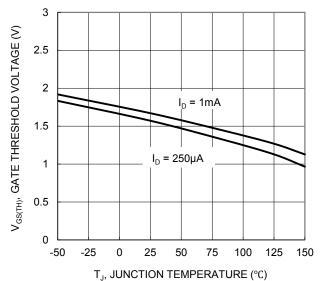
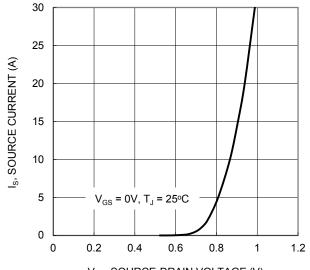


Figure 7. Gate Threshold Variation vs Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 8. Diode Forward Voltage vs. Current

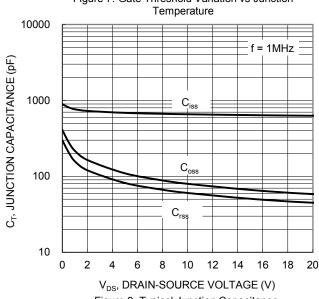


Figure 9. Typical Junction Capacitance

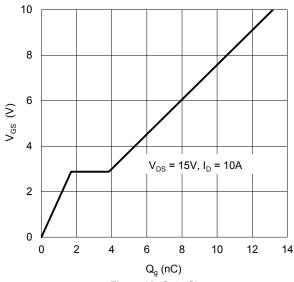


Figure 10. Gate Charge

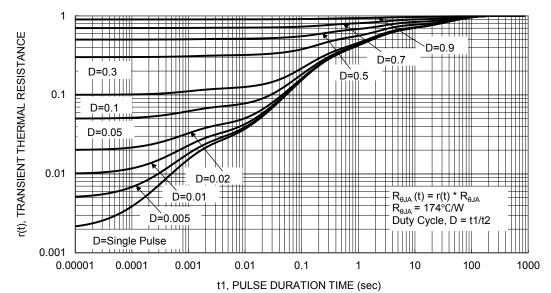


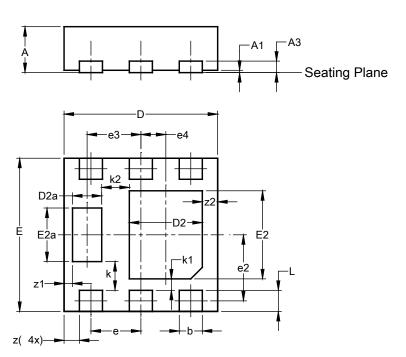
Figure 11. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

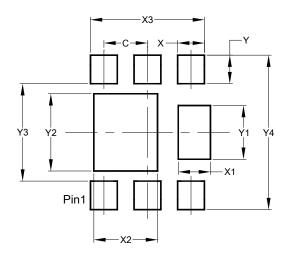


U-DFN2020-6							
	(Тур	oe F)					
Dim	Min	Тур					
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.03				
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
Е	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е		0.65 BS					
e2).863 BS					
е3		0.70 BS	-				
e4).325 BS	SC				
k		0.37 BS					
k1		0.15 BS					
k2		0.36 BS	С				
L		0.325					
Z	0.20 BSC						
z1	0.110 BSC						
z2		0.20 BS	С				
All D	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	value
Difficultions	(in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Υ	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

Value



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